DGW25N120CTL

RoHS COMPLIANT

IGBT Discrete

V_{CE}	1200	V
I_C	25	A
VCE(SAT) IC=25A	1.85	V

Applications

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-
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Features

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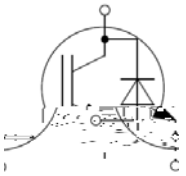
Circuit


■Maximum Ratings

Parameter	Symbol	Value	Unit

■Electrical Characteristics of the IGBT

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						

■Electrical Characteristics of the Diode

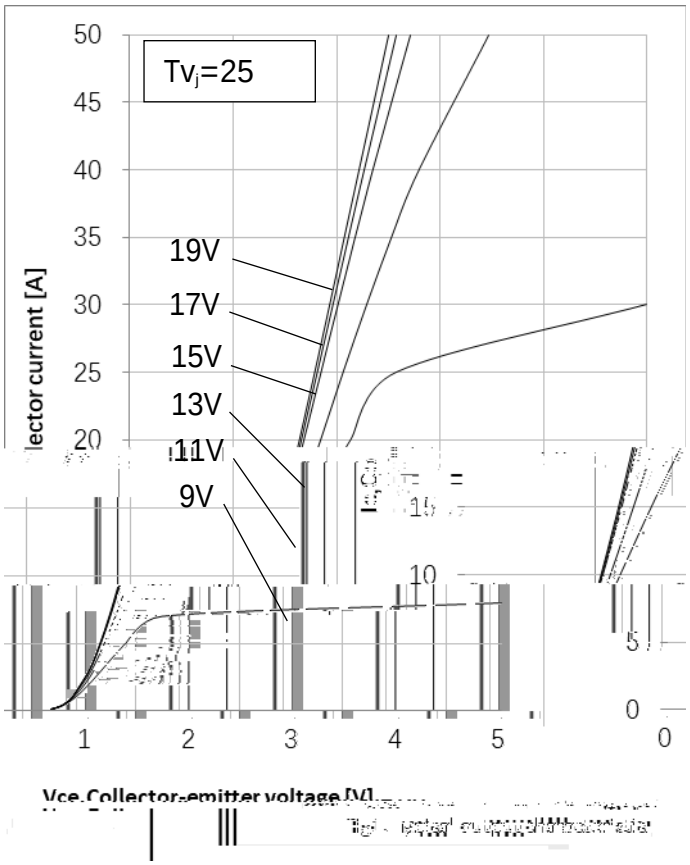
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						

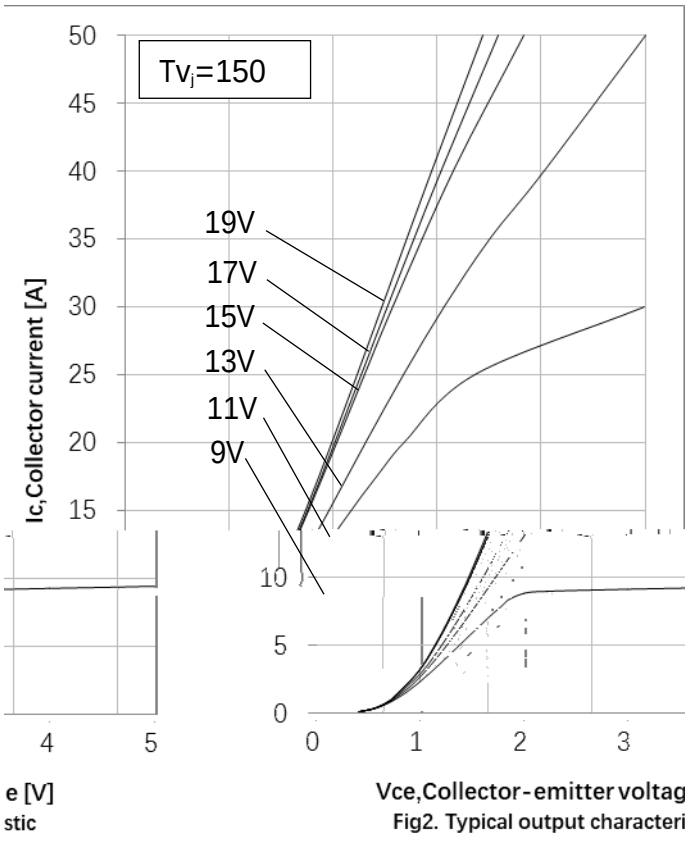
■Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25						
Dynamic , at T_j= 125						
Dynamic , at T_j= 150						

■Electrical Characteristics of the DIODE

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25						





e [V]
stic

Fig2. Typical output characteri

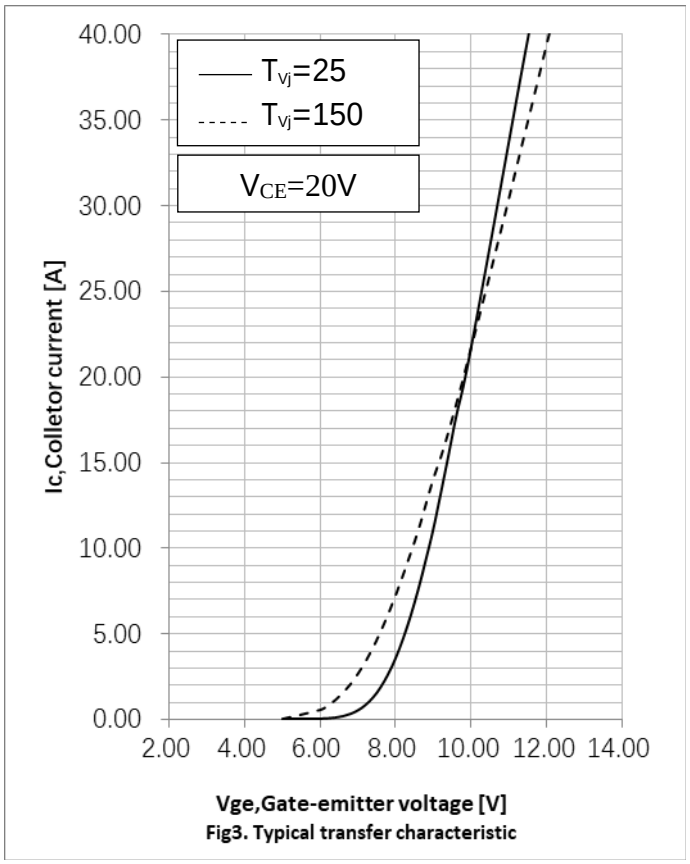


Fig3. Typical transfer characteristic

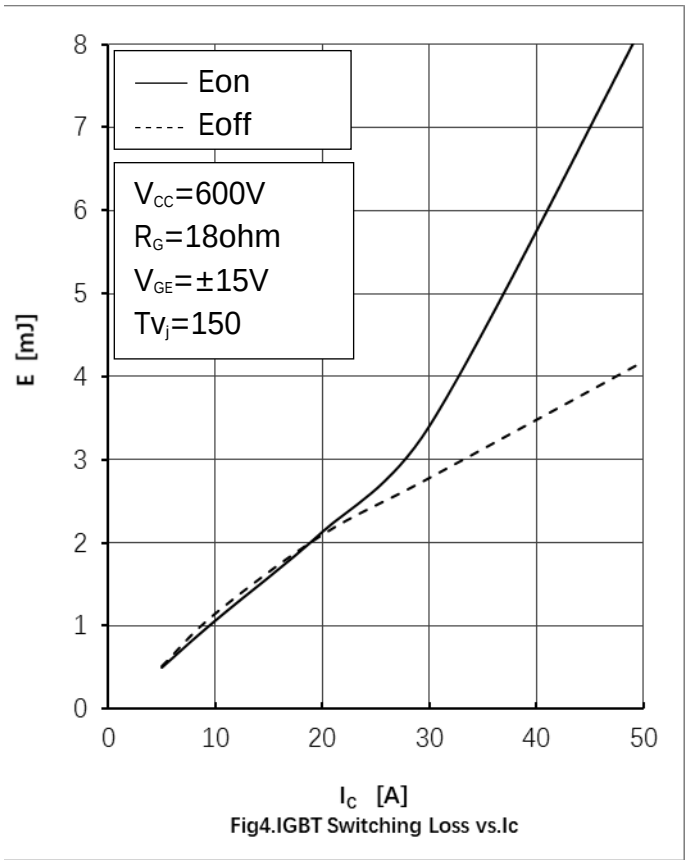


Fig4.IGBT Switching Loss vs.Ic

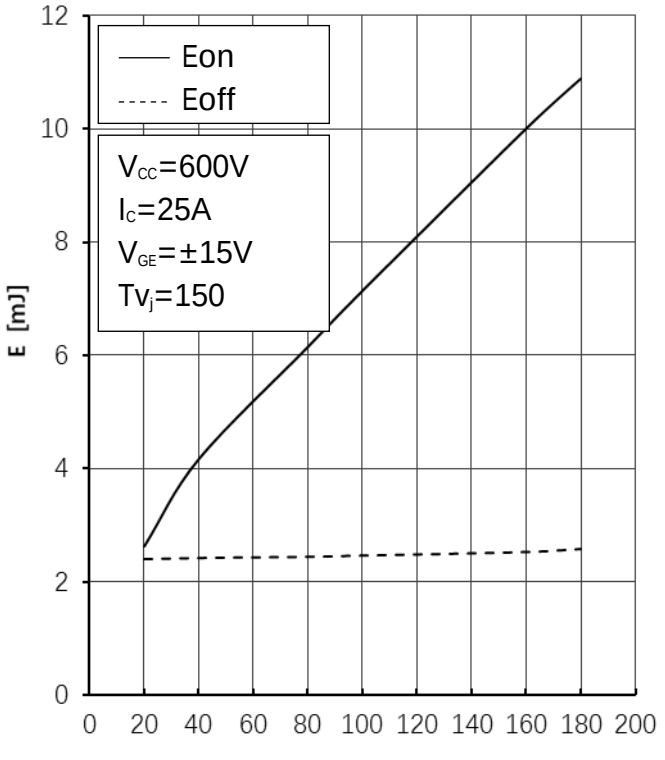


Fig5.IGBT Switching Loss vs.Rg

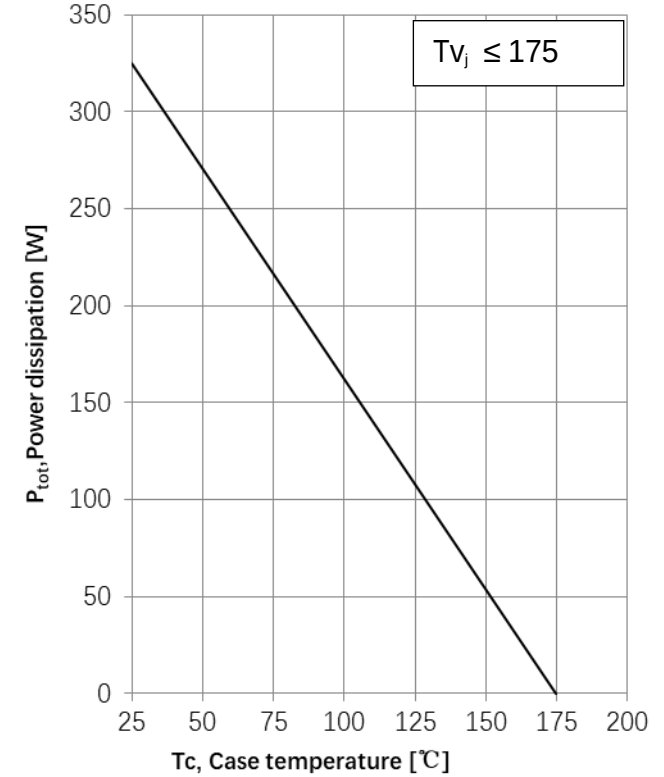


Fig6. Power dissipation as a function of case temperature (Tj≤175℃)

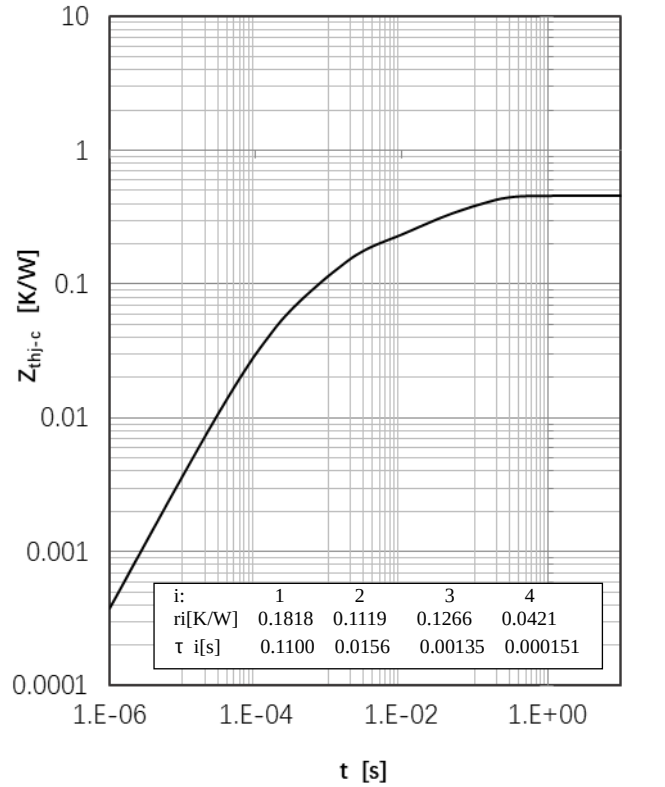


Fig 7. IGBT Transient Thermal Impedance

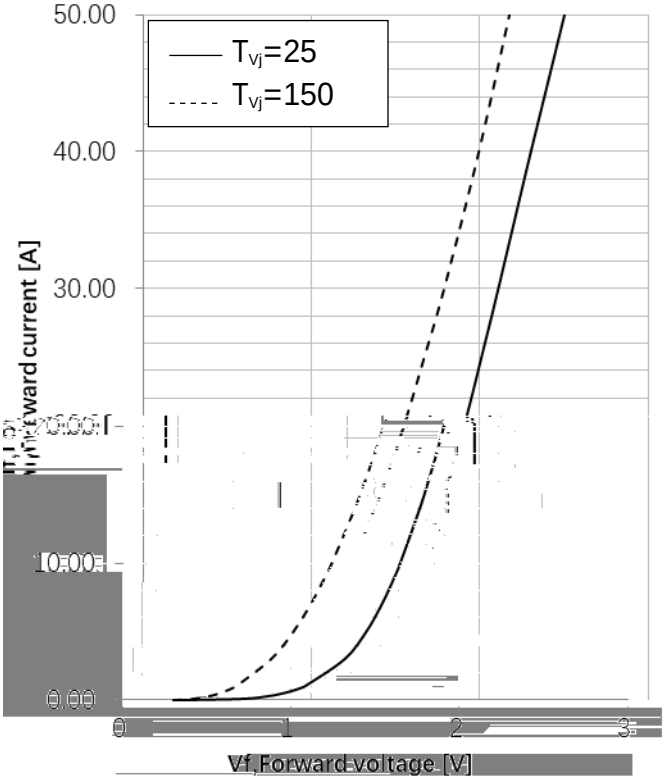
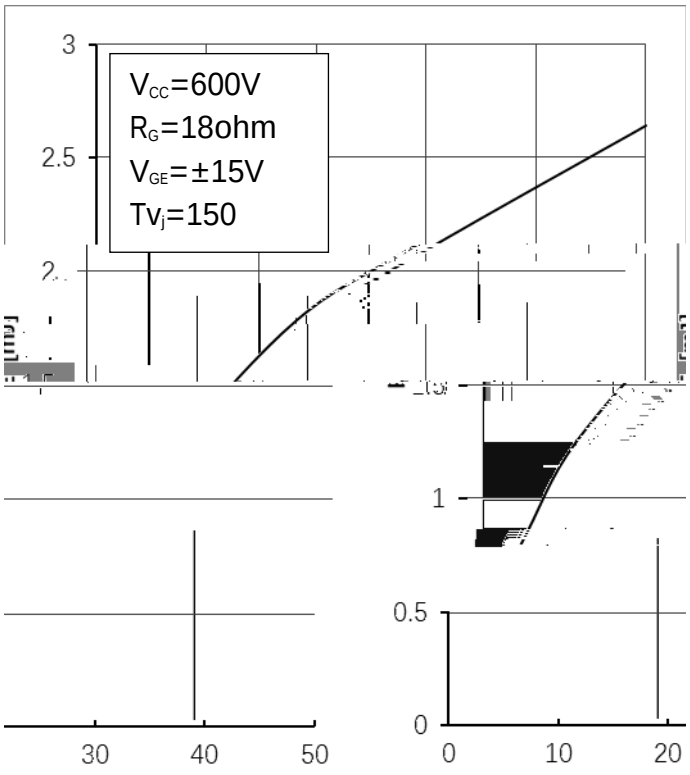


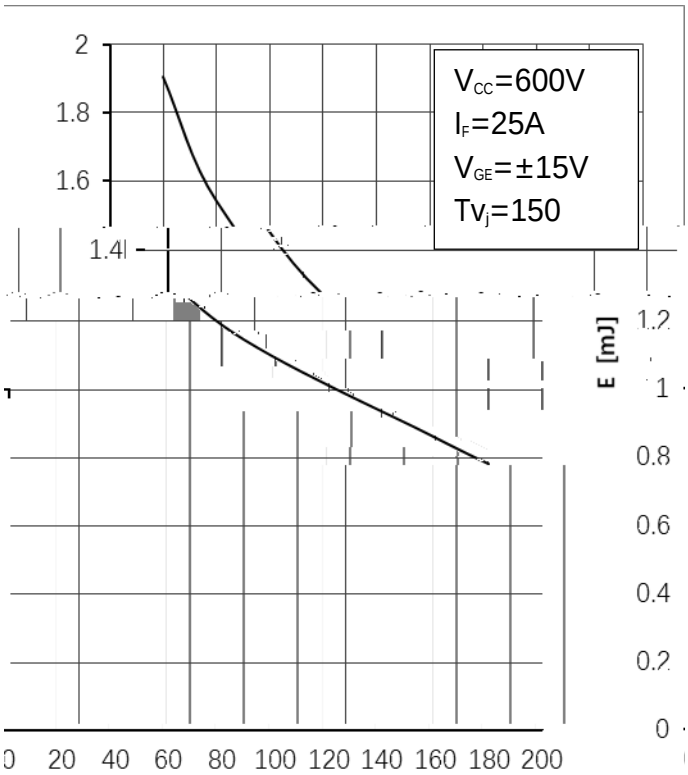
Fig8. diode forawrd current as a function of foraward voltage



I_F [A]

ching Loss(Erec) vs.I_F

Fig9.Diode Swit



R_G [ohm]

Fig10.Diode Switching Loss(Erec) vs.Rg

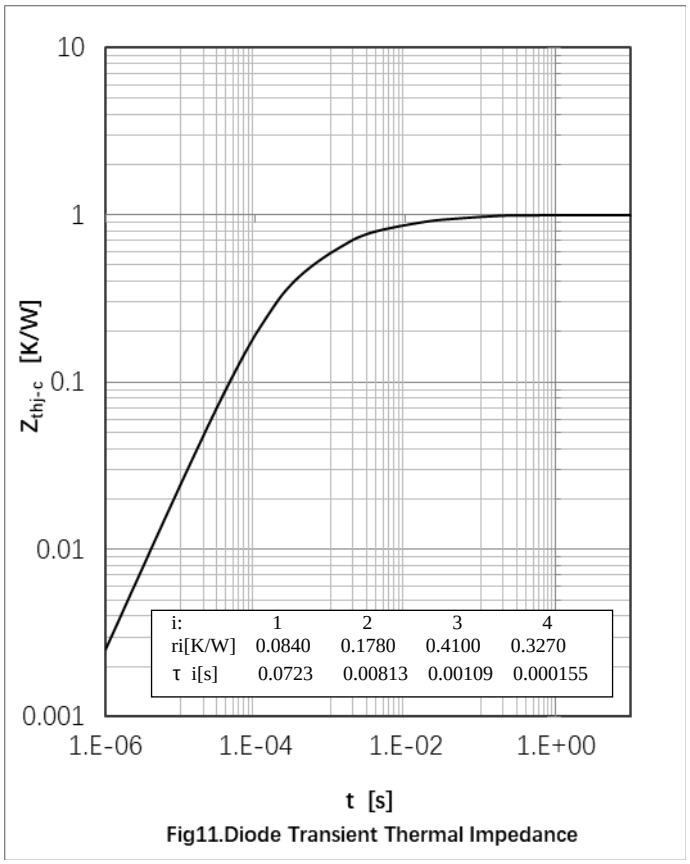
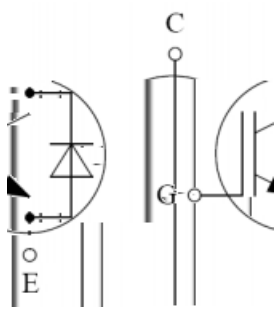


Fig11.Diode Transient Thermal Impedance

■Circuit Diagram



■Package Outline Information

CASE: TO 247